



SHEET 1 OF 1

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: MUL-003 APPLICANT(S): Yuan SERIAL NO.: 10/002,909 FILING DATE: November 2, 2001 GROUP: 2814					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
DLN	C1	Campbell et al. "Multiplication Noise of Wide-Bandwidth InP/InGaAsP/InGaAs Avalanche Photodiodes." <i>J. Lightwave Technol.</i> , Vol. 7, No. 3, pp. 473-477, 1989.							
	C2	Campbell et al. "High-Speed InP/InGaAsP/InGaAs Avalanche Photodiodes Grown by Chemical Beam Epitaxy," <i>IEEE J. Quantum Electron.</i> , Vol. 24, No. 3, pp. 496-500, 1988.							
	C3	Watanabe et al. "High-Speed and Low-Dark-Current Flip-Chip InAlAs/InAlGaAs Quaternary Well Superlattice APD's with 120 GHz Gain-Bandwidth Product," <i>IEEE Photon. Tech. Lett.</i> , Vol. 5, No. 6, pp. 675-677, 1993.							
	C4	Forrest. "Performance of $\text{In}_x\text{Ga}_{1-x}\text{As}_y\text{P}_{1-y}$ Photodiodes with Dark Current Limited by Diffusion, Generation Recombination, and Tunneling" <i>IEEE J. Quantum Electron.</i> , Vol. QE-17, No. 2, February 1981.							
	C5	Tarof et al. "Planar InP/InGaAs Avalanche Photodetectors with Partial Charge Sheet in Device Periphery," <i>Appl. Phys. Lett.</i> , Vol. 57, No. 7, pp. 670-672, 1990.							
	C6	Ekholm et al. "High Bandwidth Planar InP/InGaAs Avalanche Photodiodes," <i>IEEE Trans. On Electron Dev.</i> , Vol. 35, No. 12, pp. 2434, 1988.							
DLN	C7	Bowers et al. "Chapter 17: High-Speed Photodetectors," <i>Handbook of Optics</i> , Vol. 1, McGraw-Hill, New York, 1995.							
EXAMINER		<i>Andrew Nguyen</i>				DATE CONSIDERED 4/29/03			

2582624

RECEIVED
MAR-4 2003
TECHNOLOGY CENTER 2800